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DMV1500SD

Damper + modulation diode for CRT TV

Features

- Full kit in one package
- High breakdown voltage capability
- Very fast recovery diode
- Specified turn on switching characteristics
- Low static and peak forward voltage drop for low dissipation
- Insulated version:
 - Insulated voltage = 2000 V_{RMS}
 - Capacitance = 7 pF
- Planar technology allowing high quality and best electrical characteristics
- Outstanding performance of well proven DTV as damper and new faster Turbo 2 600 V technology as modulation

Description

High voltage semiconductor especially designed for horizontal deflection stage in standard and high resolution video display with E/W correction.

The insulated TO-220FPAB package includes both the damper diode and the modulation diode, thanks to a dedicated design.

Assembled on automated line, it offers very low dispersion values or, insulating and thermal performanes.

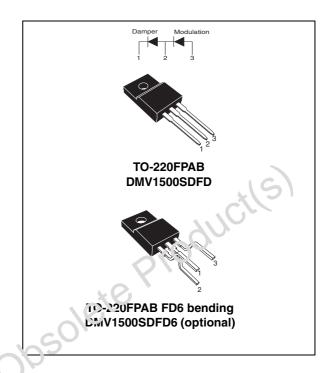


Table 1. Device summary

Symbol	Damper	Modulation
I _{F(AV)}	6 A	6 A
I _{Fpeak} (max)	12 A	12 A
V_{RRM}	1500 V	600 V
t _{rr} (typ)	150 ns	60 ns
V _F (typ)	1.1 V	1.0 V
V _{FP} (typ)	26 V	5 V

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Table 2. Absolute maximum ratings

Symbol	Paramete	r	Va	lue	Unit
Cymbol	T di dinete	•	Damper	Modulation	Onne
V _{RRM}	Repetitive peak reverse voltage		1500	600	٧
I _{Fpeak}	Peak working forward current	F = 56 kHz	12	12	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	50	50	Α
T _{stg}	Storage temperature range		-40 to	+150	°C
Tj	Maximum operating junction temperat	ure	1:	50	°C

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case thermal resistance	4.0	°C/W

Table 4. Static electrical characteristics

					Va	lue		
Symbol	Parameter	Test co	nditions	T _j = 2	25 °C	T _j = 1	25 °C	Unit
				Тур.	Max.	Тур.	Max.	
		Damper	V _R = 1500 V	110.	100	100	1000	
I _R ⁽¹⁾	Reverse leakage current	Modulation Modulation	V _R = 600 V		3	3	30	μΑ
V _F ⁽²⁾	Forward voltage drop	Damper	I _F = 6 A	1.2	1.75	1.1	1.5	٧
vF`′	Forward voilage drop	Modulation	I _F = 6 A	1.15	1.4	1	1.25	V

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

 $To \ evaluate \ the \ maximum \ conduction \ losses \ of \ the \ \textbf{damper} \ and \ \textbf{modulation} \ diodes \ use \ the \ following \ equations:$

Damper: $P = 1.2 \times I_{F(AV)} + 0.050 \times I_{F}^{2}_{(RMS)}$ **Modulation**: $P = 0.89 \times I_{F(AV)} + 0.055 \times I_{F}^{2}_{(RMS)}$

Table 5. Recovery characteristics

	16.				Va	lue		
Symbol	Parameter	Test cond	ditions	Dan	nper	Modu	lation	Unit
				Тур.	Max.	Тур.	Max.	
	Davoras resovery time	I _F = 100 mA I _R =100 mA I _{RR} = 10 mA	T _j = 25 °C	1000	2000	250	400	20
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A}$ $dI_F/dt = -50$ $A/\mu s V_R = 30 \text{ V}$	T _j = 25 °C	150	250	60	85	ns

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

DMV1500SD Characteristics

Table 6. Turn-on switching characteristics

Symbol	Parameter		Test conditions		Va	lue	Unit
Cymbol	T di dillotoi				Тур.	Max.	Oint
+.	Forward recovery time	Damper	I _F = 6 A dI _F /dt = 80 A/μs V _{FR} = 3 V	T _j = 100 °C	350	500	ns
t _{fr}	1 ofward recovery line	Modulation	$I_F = 6 \text{ A}$ $dI_F/dt = 80 \text{ A/}\mu\text{s}$ $V_{FR} = 2 \text{ V}$	T _j = 100 °C	85	125	119
V	Peak forward voltage	Damper	I _F = 6 A dI _F /dt = 80 A/μs	T _j = 100 °C	26	36	V
V _{FP}	reak ioi waru voltaye	Modulation	I _F = 6 A dI _F /dt = 80 A/μs	T _j = 100 °C	5	7.5	V

Figure 1. Power dissipation vs. peak forward Figure 2. current (triangular waveform, δ = 0.45) (damper diode)

Power dissipation vs. peak forward current (triangular waveform, δ = 0.45) (modulation diode)

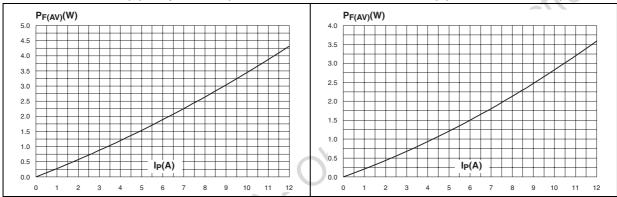
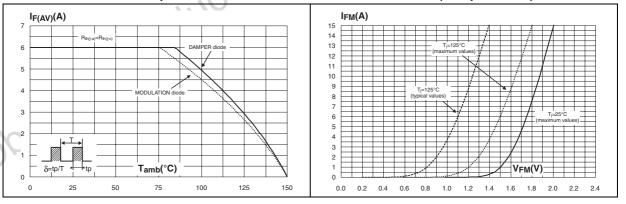


Figure 3. Average forward current vs. ambient temperature

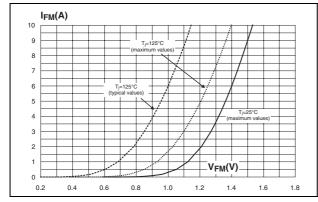
Figure 4. Forward voltage drop vs. forward current (damper diode)



Characteristics DMV1500SD

Figure 5. Forward voltage drop vs. forward current (modulation diode)

Figure 6. Relative variation of thermal impedance junction to case versus pulse duration



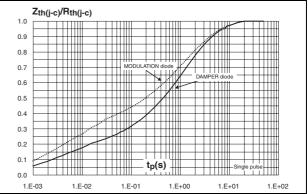
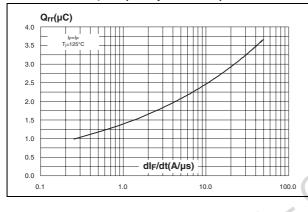


Figure 7. Reverse recovery charges vs. dl_F/dt (damper diode)

Figure 8. Reverse recovery charges vs. dl_F/dt (modulation diode)



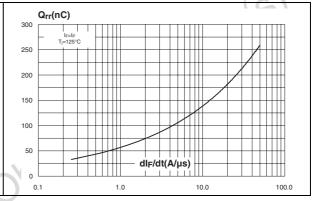
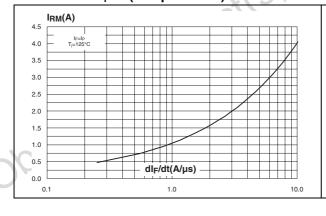
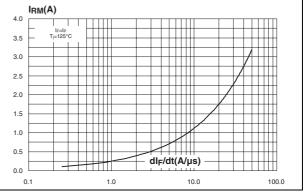


Figure 9. Peak reverse recovery current vs. dl_r/dt (damper diode)

Figure 10. Peak reverse recovery current vs. dl_E/dt (modulation diode)





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Figure 11. Transient peak forward voltage vs. dl_F/dt (damper diode, typical values)

Figure 12. Transient peak forward voltage vs. dl_F/dt (modulation diode, typical values)

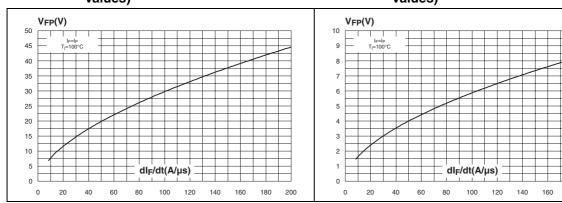


Figure 13. Forward recovery time vs. dl_F/dt (damper diode, typical values)

Figure 14. Forward recovery time vs. dl_F/dt (modulation diode, typical values)

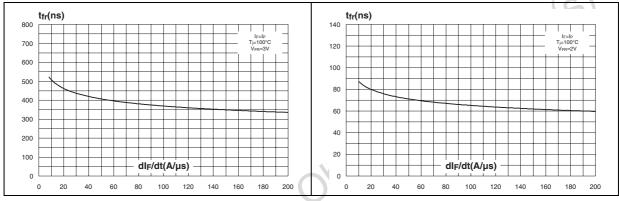
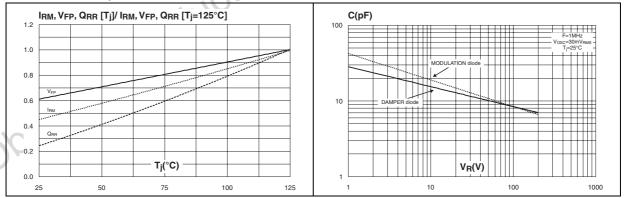


Figure 15. Relative variation of dynamic parameters vs. junction temperature

Figure 16. Junction capacitance vs. reverse voltage applied (typical values)



Package information DMV1500SD

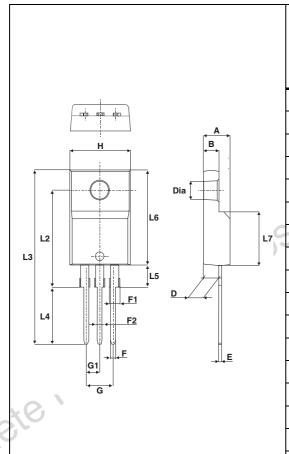
2 Package information

Epoxy meets UL94,V0

Recommended torque: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at www.st.com

Table 7. TO-220FPAB dimensions

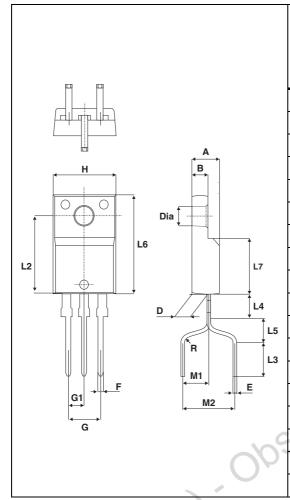


		Dimer	sions	
Ref.	Millim	neters	Inc	hes
	Min.	Max.	Min.	Max.
Α	4.4	4.6	0.173	0.181
В	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
Е	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.50	0.045	0.059
F2	1.15	1.50	0.045	0.059
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
Н	10	10.4	0.393	0.409
L2	16	Тур.	0.63	Тур.
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

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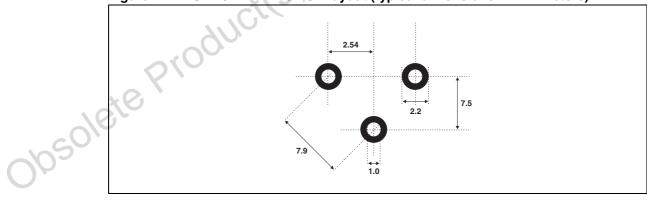
DMV1500SD Package information

Table 8. TO-220FPAB F6 dimensions



		Dimen	sions	
Ref.	Millim	eters	Inc	hes
	Min.	Max.	Min.	Max.
Α	4.4	4.9	0.173	0.192
В	2.5	2.9	0.098	0.114
D	2.45	2.75	0.096	0.108
Е	0.4	0.7	0.016	0.028
F	0.6	1	0.024	0.039
G	4.8	5.3	0.195	0.205
G1	2.2	2.95	0.094	0.106
Н	10	10.7	0.394	0.421
L2	12.7	12.8	0.500	0.504
L3	4.8	Тур.	0.189	Тур.
L4	3.4	4.8	0.150	0.165
L5	2.9	Тур.	0.114	1 Тур.
L6	15.8	16.4	0.622	0.646
L7	9	9.9	0.354	0.390
M1	3.75	Тур.	0.148	3 Тур.
M2	7	8	0.276	0.315
R	1 T	yp.	0.039	Э Тур.
Dia.	2.9	3.5	0.114	0.138

Figure 17. TO-220FPAB FD6 PCB layout (typical dimensions in millimeters)



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Ordering information DMV1500SD

3 Ordering information

Table 9. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
DMV1500SDFD	DMV1500SD	TO-220FPAB	2.4 g	50	Tube
DMV1500SDFD6	DMV1500SD	TO-220FPAB FD6	2.4 g	45	Tube

4 Revision history

Table 10. Document revision history

Date	Revision	Changes
25-Oct-2004	1	First issue
		TO-220FPAB FD6 package mechanical data changes:
		1. Ref. G: from 4.95 - 5.2 mm to 4.8 - 5.3 mm
10-Dec-2004	2	2. Ref. G1: from 2.4 - 2.7 mm to 2.2 - 2.95 mm
		3. Ref. L4: from 3.8 - 4.2 mm to 3.4 - 4.8 mm
		4. Ref L5 addition: 2.9 mm typ.
16-Mar-2005	3	I _{Fpeak} parameter included
02-Dec-2008	4	Reformatted to current standards. Updated ECOPACK statement Updated dimension illustration for TO-220FPAB FD6 in <i>Table 8</i> .
	. (6)
ie Pro	ducti	5)

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